

SANYO	No.679F	2SB775/2SD895
	2SB775 : PNP Epitaxial Planar Silicon Transistor 2SD895 : NPN Triple Diffused Planar Silicon Transistor 85V/6A, AF 35W Output Applications	

Features

- Wide ASO because of on-chip ballast resistance.
- Capable of being mounted easily because of one-point fixing type plastic molded package (Interchangeable with TO-3).
- Large current capacity ($I_C = 6A$).
- Highly resistant to breakdown due to wide ASO.

() : 2SB775

Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Collector-to-Base Voltage	V_{CB0}	(-) 100	V
Collector-to-Emitter Voltage	V_{CE0}	(-) 85	V
Emitter-to-Base Voltage	V_{EB0}	(-) 6	V
Collector Current	I_C	(-) 6	A
Collector Current (Pulse)	I_{CP}	(-) 10	A
Collector Dissipation	P_C	60	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-40 to $+150$	$^\circ C$

$T_c = 25^\circ C$

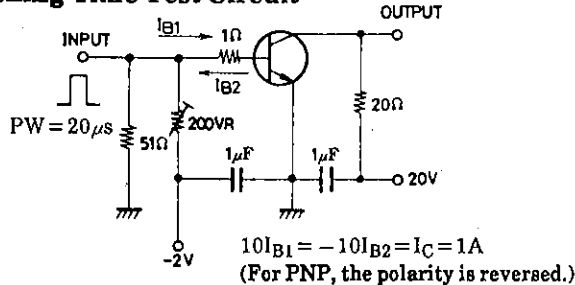
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)40V, I_E = 0$			(-) 0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-) 0.1	mA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = (-)5V, I_C = (-)1A$	60^*		200^*	
	$h_{FE}(2)$	$V_{CE} = (-)5V, I_C = (-)3A$	20			
Gain-Bandwidth Product	f_T	$V_{CE} = (-)5V, I_C = (-)1A$		(18) 15		MHz
Output Capacitance	C_{ob}	$V_{CB} = (-)10V, f = 1MHz$		160		pF
Base-to-Emitter Voltage	V_{BE}	$V_{CE} = (-)5V, I_C = (-)1A$			(-) 1.5	V
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)4A, I_B = (-)0.4A$			(-) 1.4	V
					0.9	2.0
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)5mA, I_E = 0$	(-) 100			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)5mA, R_{BE} = \infty$	(-) 85			V
		$I_C = (-)50mA, R_{BE} = \infty$	(-) 85			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)5mA, I_C = 0$	(-) 6			V
Turn-ON Time	t_{on}	See specified Test Circuit.	(0.12) 0.20			μs
Fall Time	t_f	"	(0.36) 0.82			μs
Storage Time	t_{stg}	"	(1.29) 3.88			μs

* : The 2SB775/2SD895 are classified by 1A h_{FE} as follows.

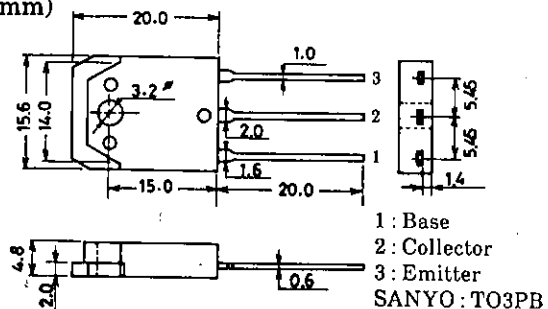
60	D	120	100	E	200
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Switching Time Test Circuit



Package Dimensions 2022A

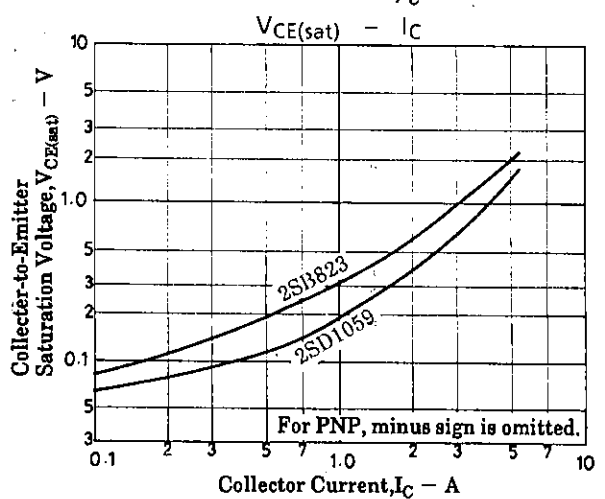
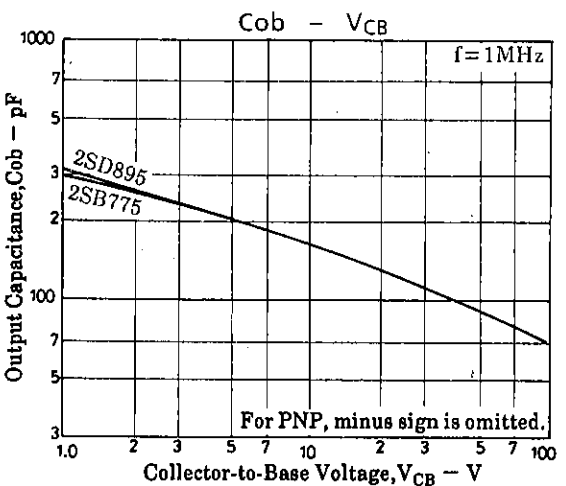
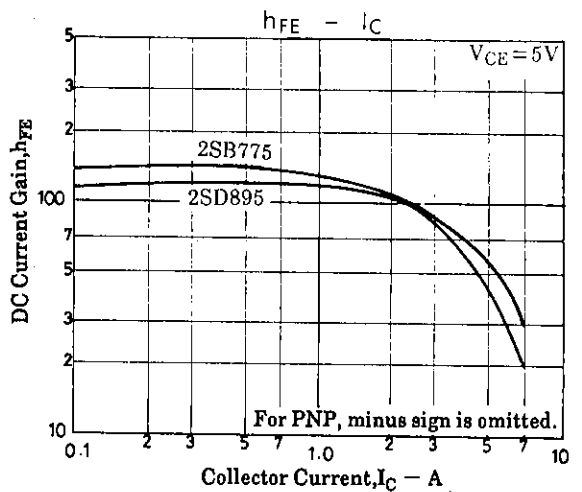
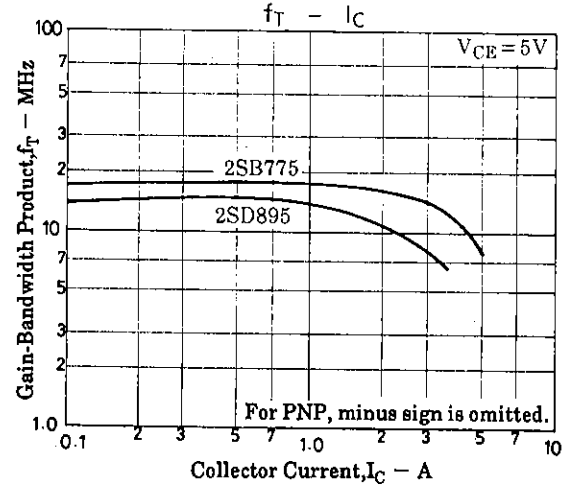
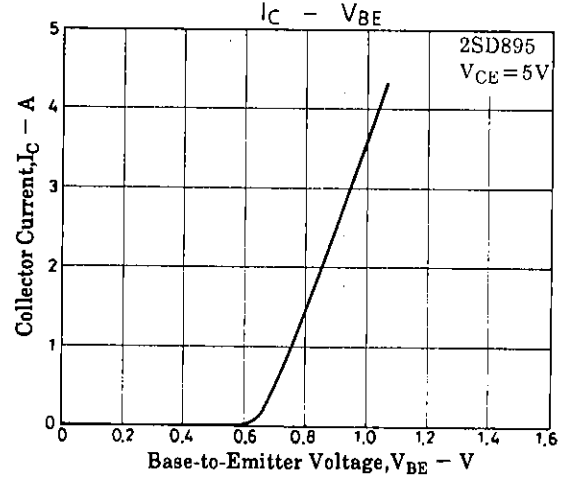
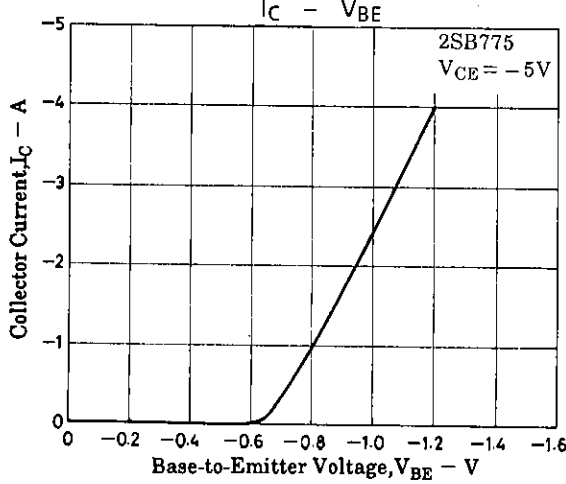
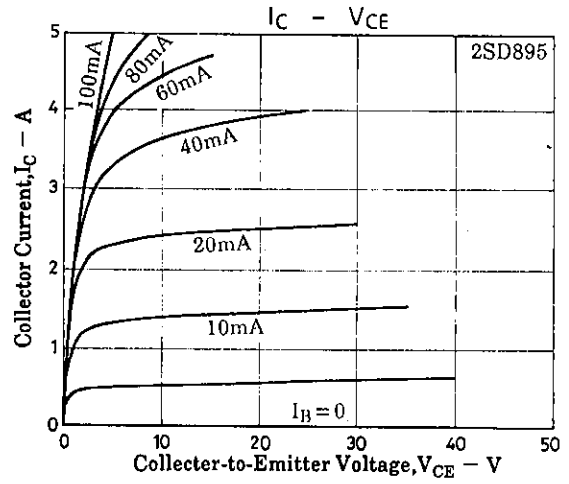
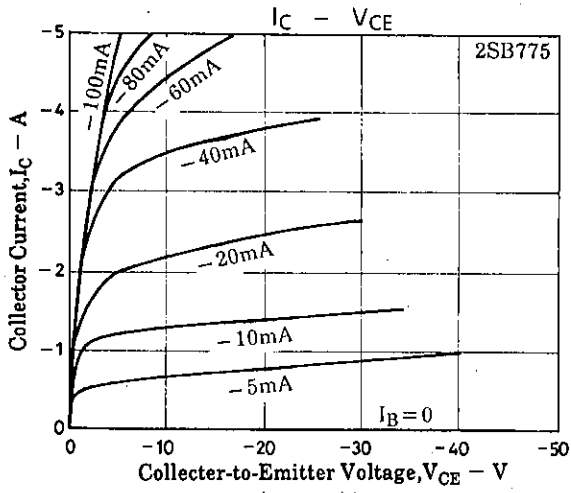
(unit : mm)



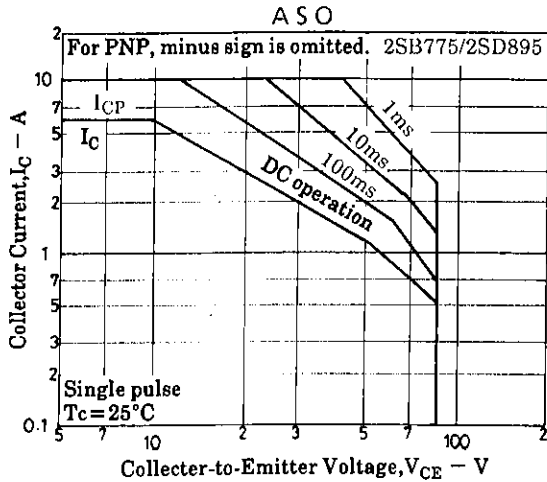
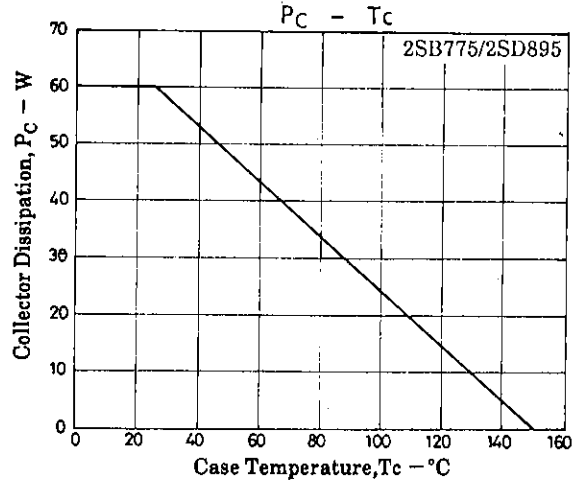
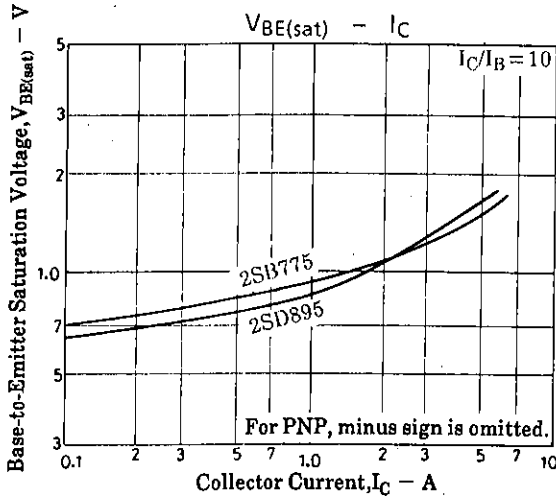
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